

FEATURES

- Ø 11.28 mm active area
- Low capacitance
- Long term stability
- High NIR sensitivity

DESCRIPTION

100 mm² Low Capacitance PIN Photodiode. Surface mount packaged with clear epoxy encapsulant.

APPLICATIONS

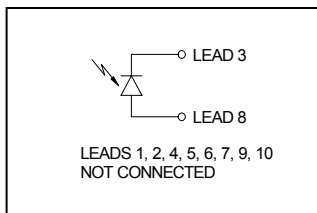
- Laser detection
- Instrumentation
- Optical remote control
- Pulsed light sensor



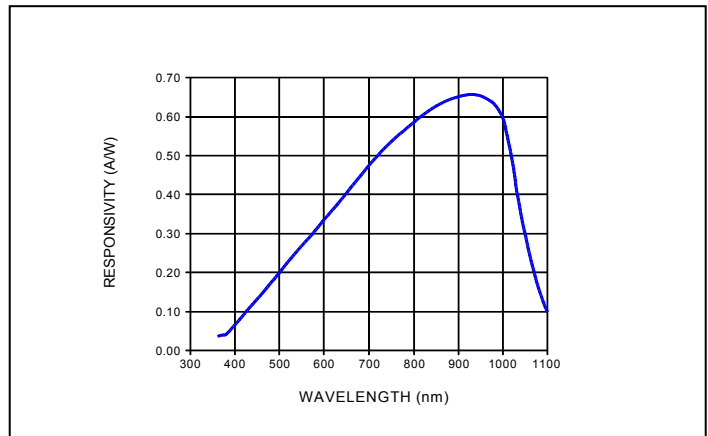
ABSOLUTE MAXIMUM RATING

SYMBOL	PARAMETER	MIN	MAX	UNITS
T _{STG}	Storage Temp	-20	+80	°C
T _{OP}	Operating Temp	-20	+60	°C
V _{R(OP)}	Reverse Operating Voltage	-	50	V
I _(PEAK)	Peak DC Current	-	10	mA

SCHEMATIC



SPECTRAL RESPONSE



ELECTRO-OPTICAL CHARACTERISTICS @ 22° C

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _D	Dark Current	V _R = 12 V	---	5.0	---	nA
C	Capacitance	V _R = 12 V	---	80.0	---	pF
	Responsivity	V _R = 0 V; λ = 950 nm	---	0.65	---	A/W
		V _R = 0 V; λ = 1064 nm	---	0.20	---	
NEP	Noise Equivalent Power	V _R = 12 V; λ = 850 nm; R _L = 50 Ω	---	4.0 X 10 ⁻¹⁴	---	W/Hz ^{1/2}
V _{BR}	Breakdown Voltage	I _R = 10 μA	30	---	---	V
t _r	Rise Time	V _R = 12 V; λ = 850 nm; R _L = 50 Ω	---	55	---	ns

Disclaimer: Due to our policy of continued development, specifications are subject to change without notice.

USA:

Pacific Silicon Sensor, Inc.
5700 Corsa Avenue, #105
Westlake Village, CA 91362 USA
Phone (818) 706-3400
Fax (818) 889-7053
Email: sales@pacific-sensor.com
www.pacific-sensor.com

International sales:

Silicon Sensor International AG
Peter-Behrens-Str. 15
D-12459 Berlin, Germany
Phone +49 (0)30-63 99 23 10
Fax +49 (0)30-63 99 23 33
Email: sales@silicon-sensor.de
www.silicon-sensor.de